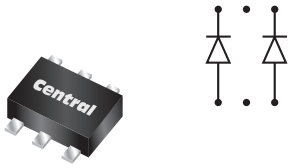
CMLD6001

SURFACE MOUNT SILICON DUAL, ISOLATED ULTRA LOW LEAKAGE SWITCHING DIODE



SOT-563 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD6001 type contains two (2) isolated silicon switching diodes, manufactured by the epitaxial planar process, epoxy molded in an SOT-563 surface mount package. These devices are designed for switching applications requiring extremely low leakage.

MARKING CODE: C6D or 6D

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Forward Surge Current, tp=1.0μs	I_{FSM}	4.0	A
Peak Forward Surge Current, tp=1.0s	I_{FSM}	1.0	A
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	500	°C/W

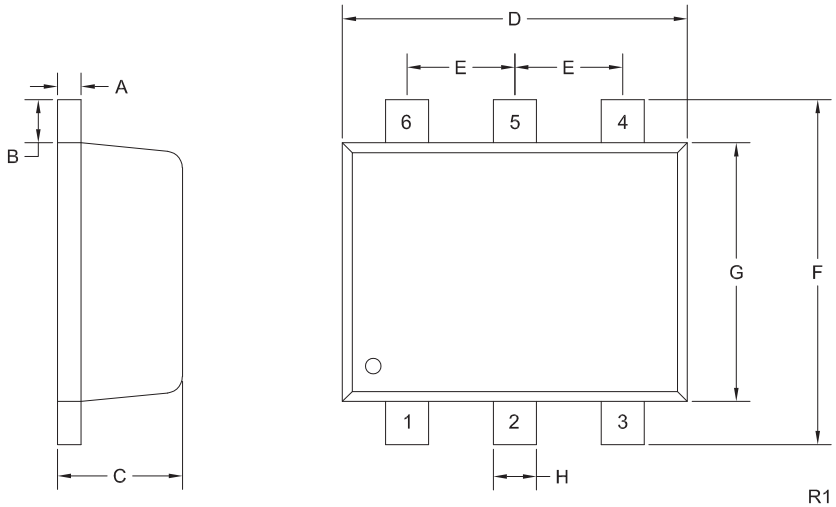
ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_R	V_R=75V		500	pA
BV_R	I_R=100μA	100		V
V_F	I_F=1.0mA		0.85	V
V_F	I_F=10mA		0.95	V
V_F	I_F=100mA		1.1	V
C_J	V_R=0, f=1.0MHz		2.0	pF
t_{rr}	I_R=I_F=10mA, I_{rr}=1.0mA, R_L=100Ω		3.0	μs

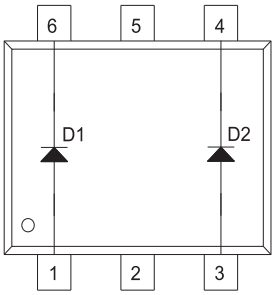
CMLD6001

SURFACE MOUNT SILICON
DUAL, ISOLATED
ULTRA LOW LEAKAGE
SWITCHING DIODE

SOT-563 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.045	0.049	1.15	1.25
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R1)

LEAD CODE:
1) Anode D1
2) NC
3) Anode D2
4) Cathode D2
5) NC
6) Cathode D1

MARKING CODE: C6D or 6D

R5 (15-September 2014)